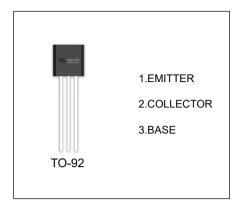


2SC1213 TRANSISTOR (NPN)

FEATURES

- Low Frequency Amplifier
- Complementary Pair With 2SA673



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC1213	TO-92	Bulk	1000pcs/Bag
2SC1213-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	35	V
V _{CEO}	Collector-Emitter Voltage	35	V
V _{EBO}	Emitter-Base Voltage	4	V
Ic	Collector Current -Continuous	0.5	Α
P _D	Collector Power Dissipation	400	mW
R _{0 JA}	Thermal Resistance rom Junction o Ambient	312	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



T_a =25 $^{\circ}$ C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.01mA,I _E =0	35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	35			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.01mA,I _C =0	4			V
Collector cut-off current	I _{CBO}	V _{CB} =20V,I _E =0			0.5	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =3V,I _C =0			0.1	μΑ
DC assessment makes	h _{FE(1)}	V _{CE} =3V, I _C =10mA	60		320	
DC current gain	h _{FE(2)}	V _{CE} =3V, I _C =500mA	10			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =150mA,I _B =15mA			0.6	V
Base-emitter voltage	V _{BE}	V _{CE} =3V, I _C =10mA			0.75	V

CLASSIFICATION OF h_{FE(1)}

RANK	В	С	D
RANGE	60-120	100-200	160-320